

# ZXTP25040DFH

## 40V SOT23 PNP medium power transistor

### Summary

$BV_{CEO} > -40V$

$BV_{ECO} > -3V$  ;

$I_{C(CONT)} = -3A$

$R_{CE(sat)} = 55\ m\Omega$  ;

$V_{CE(sat)} < -85mV @ 1A$  ;

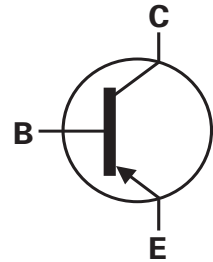
$P_D = 1.25W$

Complementary part number ZXTN25040DFH



### Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

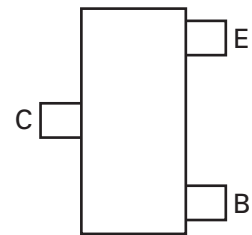


### Features

- High power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 3V reverse blocking voltage

### Applications

- MOSFET and IGBT gate driving
- DC - DC converters
- Motor drive
- High side driver



Pinout - top view

### Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP25040DFHTA	7	8mm	3000

### Device marking

024

# ZXTP25040DFH

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	$V_{CBO}$	-45	V
Collector-emitter voltage (forward blocking)	$V_{CEO}$	-40	V
Emitter-collector voltage (reverse blocking)	$V_{ECO}$	-3	V
Emitter-base voltage	$V_{EBO}$	-7	V
Continuous collector current <sup>(b)</sup>	$I_C$	-3	A
Peak pulse current	$I_{CM}$	-9	A
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(a)</sup> linear derating factor	$P_D$	0.73 5.84	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(b)</sup> linear derating factor	$P_D$	1.05 8.4	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(c)</sup> linear derating factor	$P_D$	1.25 9.6	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(d)</sup> linear derating factor	$P_D$	1.81 14.5	W mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	-55 to 150	°C

## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	171	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	119	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\theta JA}$	100	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\theta JA}$	69	°C/W

### NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

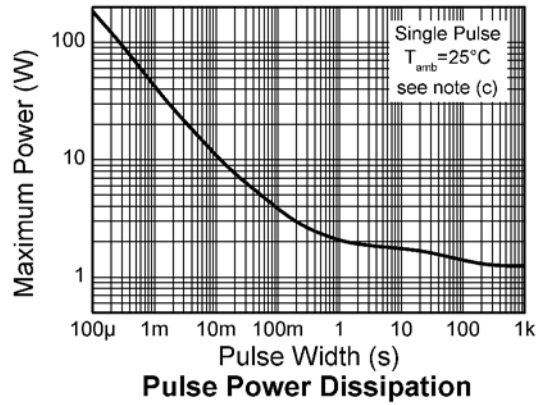
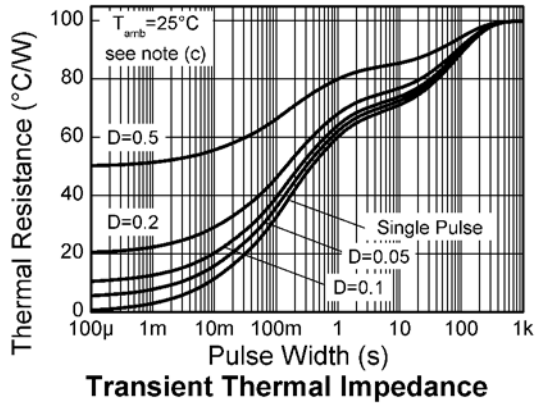
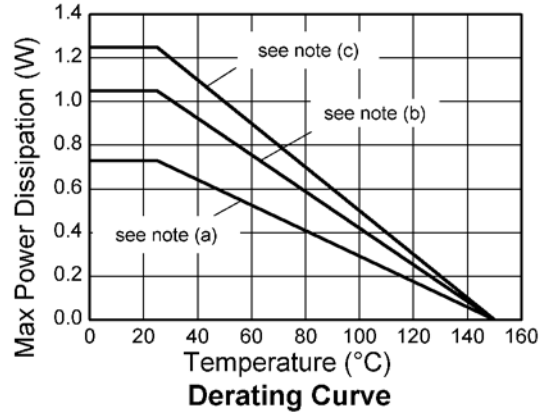
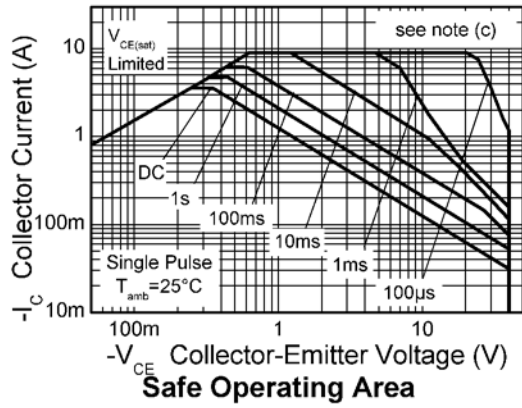
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at  $t < 5\text{sec}$ .

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## Characteristics



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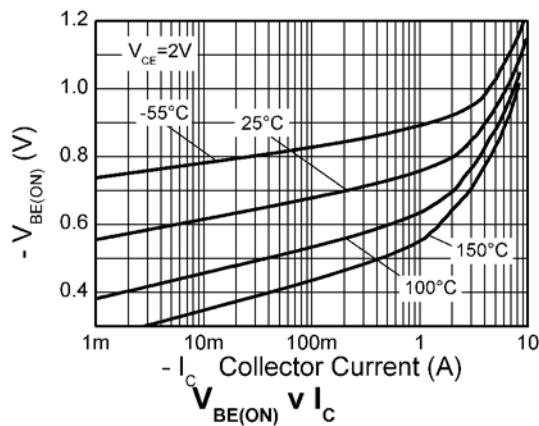
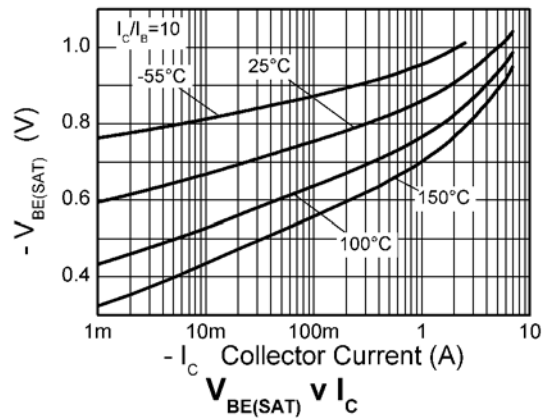
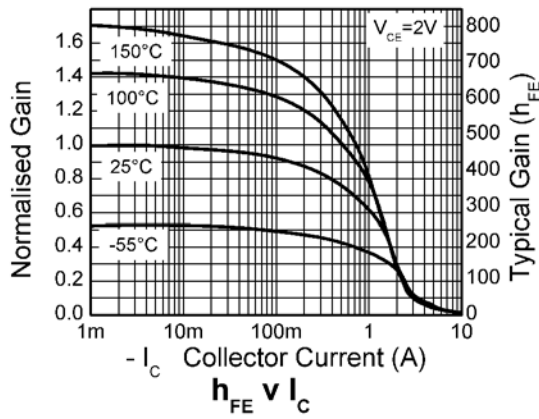
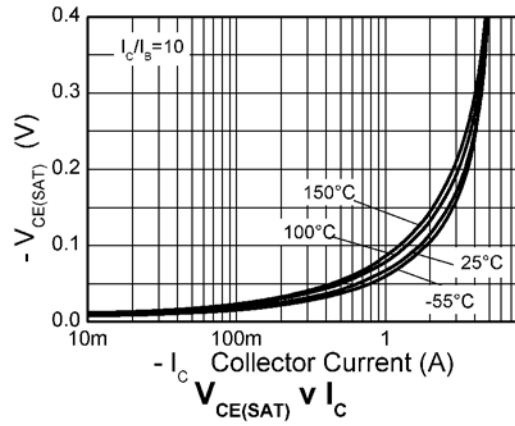
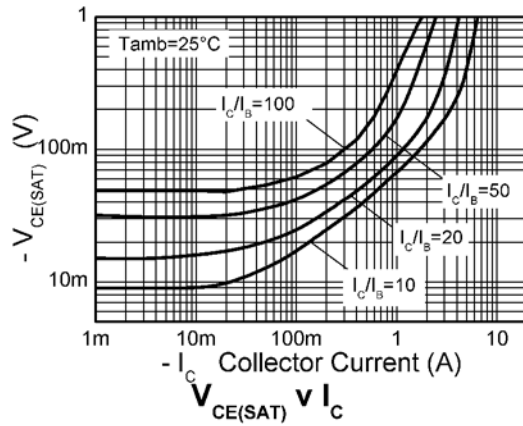
## Electrical characteristics (at $T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	-45	-75		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage (base open)	$BV_{CEO}$	-40	-65		V	$I_C = -10\text{mA}^{(*)}$
Emitter-collector breakdown voltage (reverse blocking)	$BV_{ECO}$	-3	-8.7		V	$I_E = -100\mu\text{A}$
Emitter-base breakdown voltage	$BV_{EBO}$	-7	-8.2		V	$I_E = -100\mu\text{A}$
Collector cut-off current	$I_{CBO}$		<-1	-50 -0.5	nA $\mu\text{A}$	$V_{CB} = -45\text{V}$ $V_{CB} = -45\text{V}, T_{amb} = 100^{\circ}\text{C}$
Emitter cut-off current	$I_{EBO}$		<-1	-50	nA	$V_{EB} = -5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		-170 -65 -165	-260 -85 -220	mV mV mV	$I_C = -1\text{A}, I_B = -20\text{mA}^{(*)}$ $I_C = -1\text{A}, I_B = -100\text{mA}^{(*)}$ $I_C = -3\text{A}, I_B = -300\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		-930	-1000	mV	$I_C = -3\text{A}, I_B = -300\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		-830	-900	mV	$I_C = -3\text{A}, V_{CE} = -2\text{V}^{(*)}$
Static forward current transfer ratio	$h_{FE}$	300 200 30	450 300 60	900		$I_C = -10\text{mA}, V_{CE} = -2\text{V}^{(*)}$ $I_C = -1\text{A}, V_{CE} = -2\text{V}^{(*)}$ $I_C = -3\text{A}, V_{CE} = -2\text{V}^{(*)}$
Transition frequency	$f_T$		270		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output capacitance	$C_{OBO}$		17.4		pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}^{(*)}$
Turn-on time	$t_{(on)}$		75.5		ns	$V_{CC} = -15\text{V}, I_C = -750\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$ .
Turn-off time	$t_{(off)}$		320		ns	

### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## Typical characteristics



# ZXTP25040DFH

## Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
c	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
e	0.95 NOM		0.037 NOM		-	-	-	-	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Kustermann-Park D-81541 München Germany	Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA	Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

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### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

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